ABSTRACT

A method of forming a wiring of an aluminum material having a low-temperature sputtering process for sputtering an aluminum material (aluminum or an alloy composed mainly of aluminum) at a temperature of below 300°C and a high-temperature sputtering process for sputtering at or above 300°C, a film thickness (A) obtained by the low-temperature sputtering process is larger than a film thickness (B) obtained by the high-temperature sputtering process, and a deposition rate at high temperature sputtering is a rate which does not deteriorate the shape of a registration accuracy measurement mark, preferably 200 nm/min or less.